



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Features

- $BV_{CEO} > 180V$
- $I_C = 0.5A$ high Continuous Collector Current
- $I_{CM} = 1A$ Peak Pulse Current
- High gain device > 500 at $I_C = 100mA$

Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 ^(e3)
- Weight: 0.34 grams (approximate)

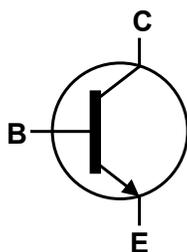
Applications

- Voltage Regulator Transistors
- Startup Switches
- Darlington Replacement
- DC Fans
- Relays and Solenoid Driving

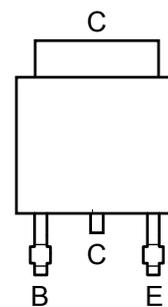
TO252 (DPAK)



Top View



Equivalent Circuit



Top View
Pin-Out

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage	V_{CEO}	180	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	0.5	A
Peak Pulse Current	I_{CM}	1	A
Peak Base Current	I_{BM}	0.5	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

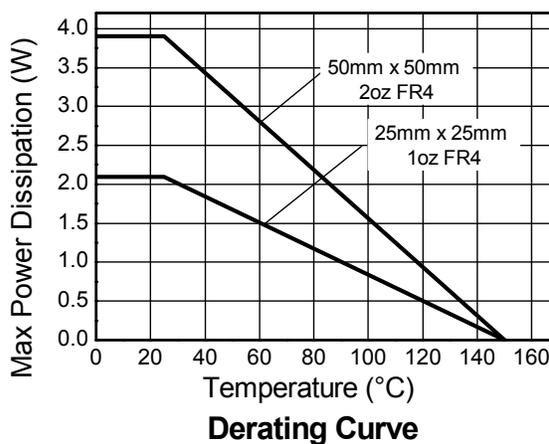
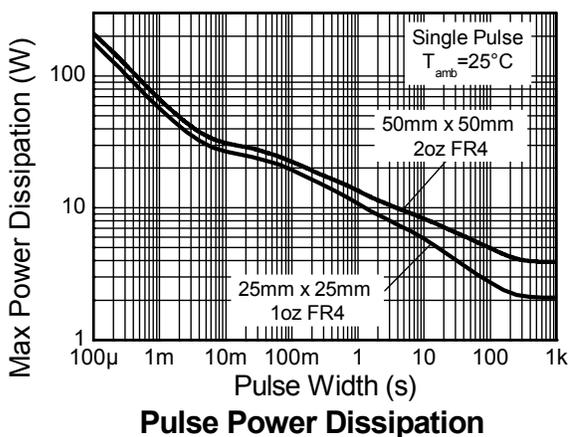
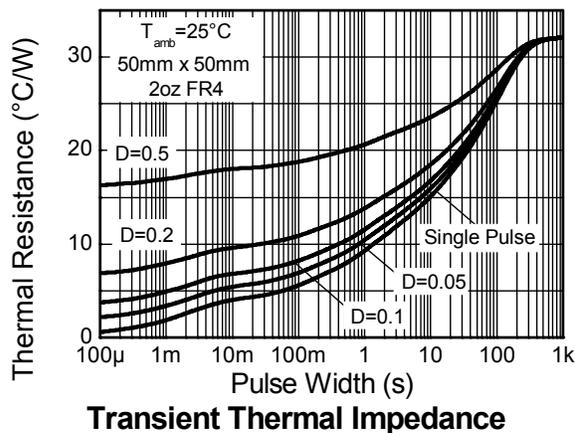
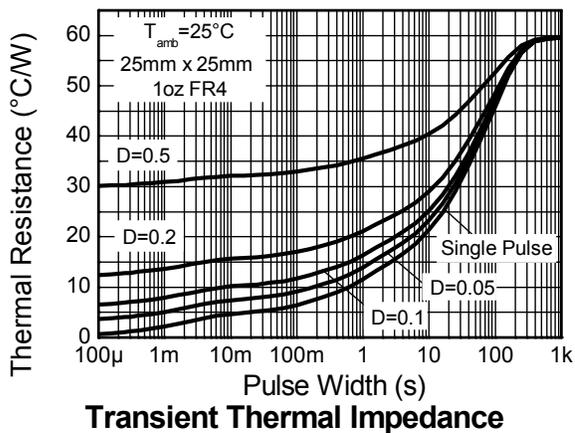
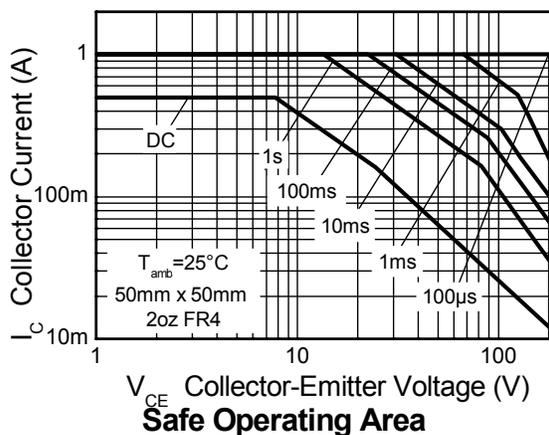
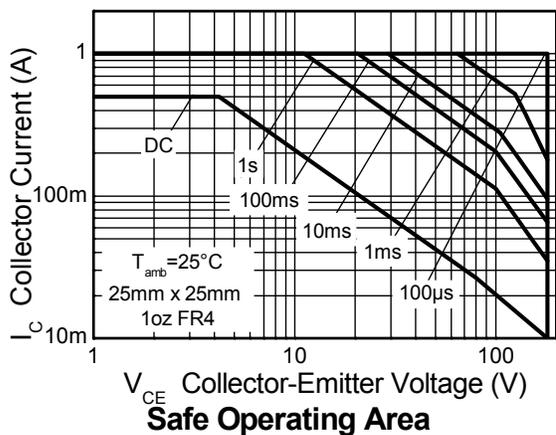
Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	(Note 5)	3.9
		(Note 6)	2.1
		(Note 7)	1.6
Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	(Note 5)	32
		(Note 6)	59
		(Note 7)	80
Thermal Resistance, Junction to Leads	$R_{\theta JL}$	8.4	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	14.6	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Same as note (5), except mounted on 25mm x 25mm 1oz copper.
 7. Same as note (5), except mounted on minimum recommended pad (MRP) layout.
 8. Thermal resistance from junction to solder-point (on the exposed collector pad).
 9. Thermal resistance from junction to the top of the case.
 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

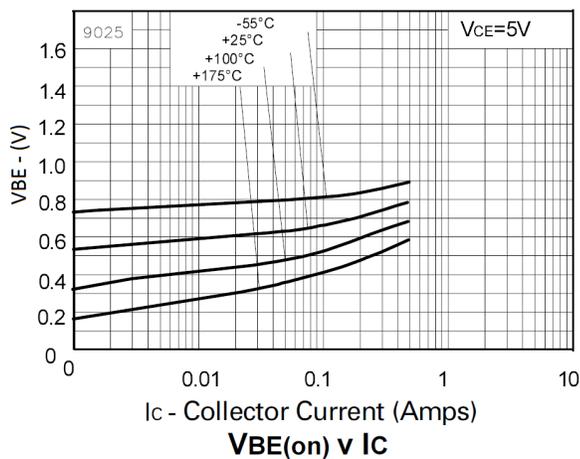
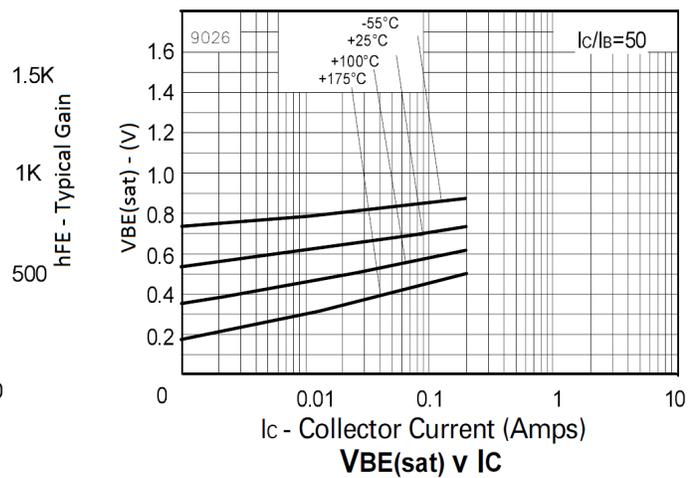
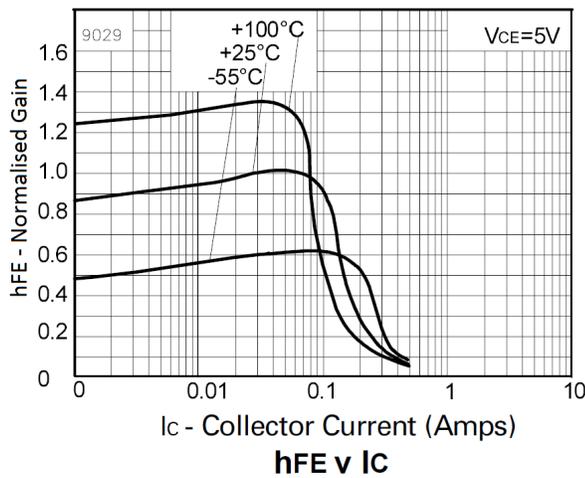
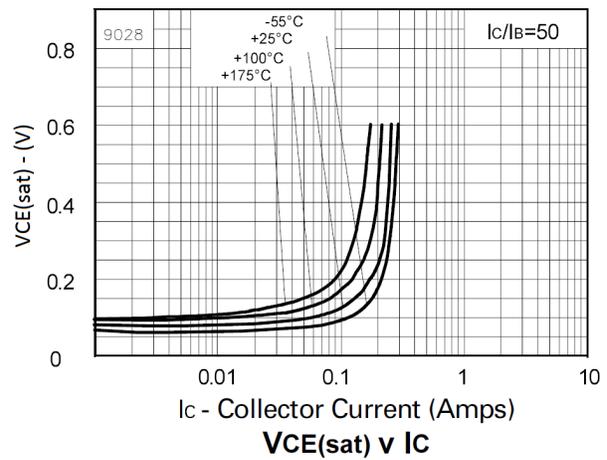
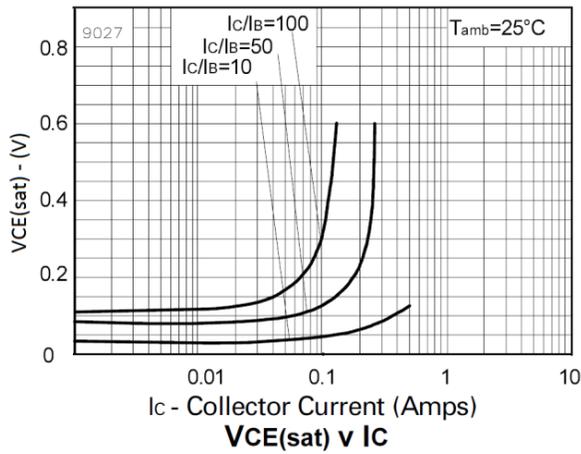


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

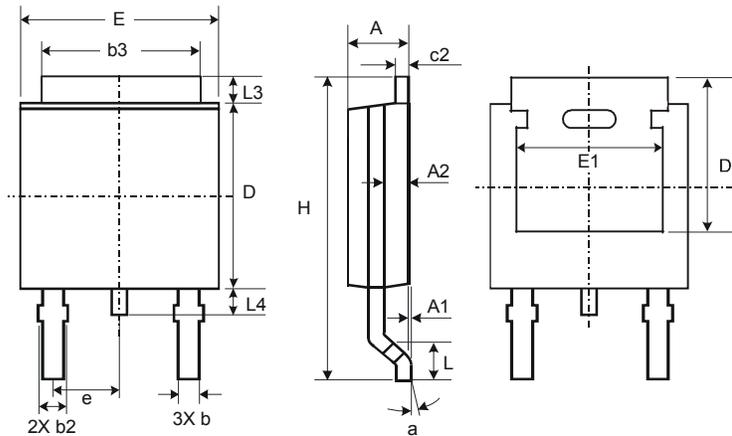
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	180	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	180	—	—	V	I _C = 1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	—	—	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}	—	—	100	nA	V _{CB} = 140V
Emitter Cutoff Current	I _{EBO}	—	—	100	nA	V _{EB} = 5V
DC Current Gain (Note 11)	h _{FE}	500 150	— —	— —		I _C = 100mA, V _{CE} = 5V I _C = 200mA, V _{CE} = 5V
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	— — —	— — —	200 200 250	mV	I _C = 50mA, I _B = 0.5mA I _C = 100mA, I _B = 2.0mA I _C = 200mA, I _B = 5.0mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	—	—	900	mV	I _C = 200mA, I _B = 5mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	—	—	900	mV	I _C = 200mA, V _{CE} = 5V
Input Capacitance	C _{ibo}	—	200	—	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance	C _{obo}	—	6	—	pF	V _{CE} = 10V, f = 1MHz
Current Gain-Bandwidth Product	f _T	70	—	—	MHz	V _{CE} = 5V, I _C = 50mA, f=50MHz
Turn-On Time	t _{on}	—	80	—	ns	V _{CC} = 50V, I _C = 100mA
Turn-Off Time	t _{off}	—	4,400	—	ns	I _{B1} = -I _{B2} = 10mA

Note: 11. Measured under pulsed conditions. Pulse width ≤ 300 μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

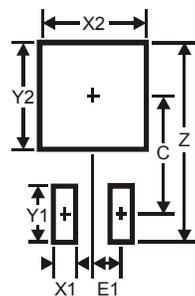


Package Outline Dimensions



TO252			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
C	6.9
E1	2.3

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.